\_F155/LF156/LF157 Series Monolithic JFET Input Operational Amplifiers

# LF155/LF156/LF157 Series Monolithic JFET Input Operational Amplifiers

#### **General Description**

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FETTM Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or commonmode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

#### **Advantages**

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

#### **Applications**

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers
- Logarithmic amplifiers

- Photocell amplifiers
- Sample and Hold circuits

#### **Common Features**

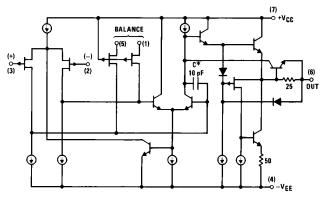
(LF155A, LF156A, LF157A)

■ Low input bias current	30 pA
■ Low Input Offset Current	3 pA
■ High input impedance	$10^{12}\Omega$
■ Low input offset voltage	1 mV
■ Low input offset voltage temp. drift	3 μV/°C
■ Low input noise current	0.01 pA/√ <del>Hz</del>
■ High common-mode rejection ratio	100 dB
■ Large dc voltage gain	106 dB

#### **Uncommon Features**

	LF155A	LF156A	LF157A (A <sub>V</sub> =5)	Units
■ Extremely fast settling time to 0.01%	4	1.5	1.5	μS
■ Fast slew				
rate	5	12	50	V/μs
<ul><li>Wide gain bandwidth</li></ul>	2.5	5	20	MHz
Low input noise voltage	20	12	12	nV/√ <del>Hz</del>

#### **Simplified Schematic**



\*3 pF in LF157 series.

TL/H/5646-1

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#### **Absolute Maximum Ratings**

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

(Note 8)

,	LF155A/6A/7A	LF155/6/7	LF355B/6B/7B LF255/6/7	LF355/6/7 LF355A/6A/7A
Supply Voltage	$\pm22V$	$\pm22V$	$\pm$ 22V	$\pm18V$
Differential Input Voltage	$\pm40V$	$\pm 40V$	$\pm40V$	$\pm30V$
Input Voltage Range (Note 2)	$\pm20V$	$\pm 20 V$	$\pm20V$	$\pm16V$
Output Short Circuit Duration	Continuous	Continuous	Continuous	Continuous
T <sub>JMAX</sub> H-Package N-Package M-Package	150°C	150°C	115°C 100°C 100°C	115°C 100°C 100°C
Power Dissipation at T <sub>A</sub> = 25°C (Notes	1 and 9)			
H-Package (Still Air) H-Package (400 LF/Min Air Flow) N-Package M-Package	560 mW 1200 mW	560 mW 1200 mW	400 mW 1000 mW 670 mW 380 mW	400 mW 1000 mW 670 mW 380 mW
Thermal Resistance (Typical) $\theta_{ m JA}$ H-Package (Still Air) H-Package (400 LF/Min Air Flow) N-Package M-Package	160°C/W 65°C/W	160°C/W 65°C/W	160°C/W 65°C/W 130°C/W 195°C/W	160°C/W 65°C/W 130°C/W 195°C/W
(Typical) $ heta_{ m JC}$ H-Package	23°C/W	23°C/W	23°C/W	23°C/W
Storage Temperature Range	-65°C to +150°C	-65°C to +150°C	-65°C to +150°C	-65°C to +150°C
Soldering Information (Lead Temp.) Metal Can Package Soldering (10 sec.)	300°C	300°C	300°C	300°C
Dual-In-Line Package Soldering (10 sec.) Small Outline Package		260°C	260°C	260°C
Vapor Phase (60 sec.) Infrared (15 sec.)			215°C 220°C	215°C 220°C
See AN-450 "Surface Mounting Method mount devices. ESD tolerance	ds and Their Effect on F	Product Reliability'' for o	other methods of solde	ring surface
(100 pF discharged through 1.5 k $\Omega$ )	1000V	1000V	1000V	1000V

# DC Electrical Characteristics (Note 3) $T_A = T_j = 25^{\circ}C$

Cumbal	Davameter	Conditions	LF1	155A/6A	/7A	LF3	355A/6A	/7A	Unite
Symbol	Parameter	Conditions	Min	Тур	Max	Min	Тур	Max	Units
V <sub>OS</sub>	Input Offset Voltage	R <sub>S</sub> =50Ω, T <sub>A</sub> =25°C Over Temperature		1	2 2.5		1	2 2.3	mV mV
ΔV <sub>OS</sub> /ΔT	Average TC of Input Offset Voltage	$R_S = 50\Omega$		3	5		3	5	μV/°C
$\Delta TC/\Delta V_{OS}$	Change in Average TC with V <sub>OS</sub> Adjust	R <sub>S</sub> =50Ω, (Note 4)		0.5			0.5		μV/°C per mV
Ios	Input Offset Current	T <sub>j</sub> =25°C, (Notes 3, 5)		3	10		3	10	pА
		Tj≤T <sub>HIGH</sub>			10			1	nA
IB	Input Bias Current	T <sub>j</sub> =25°C, (Notes 3, 5)		30	50		30	50	pА
		$T_j \le T_{HIGH}$			25			5	nA
R <sub>IN</sub>	Input Resistance	T <sub>j</sub> =25°C		10 <sup>12</sup>			10 <sup>12</sup>		Ω
A <sub>VOL</sub>	Large Signal Voltage	$V_S = \pm 15V, T_A = 25^{\circ}C$	50	200		50	200		V/mV
	Gain	$V_O = \pm 10V$ , $R_L = 2k$ Over Temperature	25			25			V/mV
Vo	Output Voltage Swing	$V_S = \pm 15V, R_L = 10k$ $V_S = \pm 15V, R_L = 2k$	±12 ±10	±13 ±12		±12 ±10	±13 ±12		V V

# $\label{eq:DC Electrical Characteristics} \textbf{(Note 3)} \, \textbf{T}_{\textbf{A}} = \textbf{T}_{j} = 25^{\circ} \textbf{C} \, \textbf{(Continued)}$

Symbol	Parameter	Conditions		155A/6A/7	7 <b>A</b>	LF	Units		
Syllibol	Parameter	Conditions	Min	Тур	Max	Min	Тур	Max	Units
V <sub>CM</sub>	Input Common-Mode Voltage Range	V <sub>S</sub> = ± 15V	±11	+ 15.1 -12		±11	+ 15.1 - 12		V V
CMRR	Common-Mode Rejection Ratio		85	100		85	100		dB
PSRR	Supply Voltage Rejection Ratio	(Note 6)	85	100		85	100		dB

# AC Electrical Characteristics $T_A = T_j = 25^{\circ}\text{C}, V_S = \pm\,15\text{V}$

Cumbal	Davamatav	Conditions	LF	155A/3	55A	LF	156A/3	56A	LF	157A/3	57A	Units
Symbol	Parameter	Parameter Conditions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Units
SR	Slew Rate	LF155A/6A; A <sub>V</sub> =1, LF157A; A <sub>V</sub> =5	3	5		10	12		40	50		V/μs V/μs
GBW	Gain Bandwidth Product			2.5		4	4.5		15	20		MHz
t <sub>s</sub>	Settling Time to 0.01%	(Note 7)		4			1.5			1.5		μs
e <sub>n</sub>	Equivalent Input Noise Voltage	$R_S = 100\Omega$ f = 100  Hz f = 1000  Hz		25 20			15 12			15 12		nV/√ <del>Hz</del> nV/√ <del>Hz</del>
i <sub>n</sub>	Equivalent Input Noise Current	f=100 Hz f=1000 Hz		0.01 0.01			0.01 0.01			0.01 0.01		pA/√ <del>Hz</del> pA/√ <del>Hz</del>
C <sub>IN</sub>	Input Capacitance			3			3			3		pF

#### **DC Electrical Characteristics** (Note 3)

Symbol	Parameter	Conditions	L	F155/6/	7		F255/6/ 55B/6B		L	F355/6/	7	Units
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
V <sub>OS</sub>	Input Offset Voltage	R <sub>S</sub> =50Ω, T <sub>A</sub> =25°C Over Temperature		3	5 7		3	5 6.5		3	10 13	mV mV
$\Delta V_{OS}/\Delta T$	Average TC of Input Offset Voltage	$R_S = 50\Omega$		5			5			5		μV/°C
ΔTC/ΔV <sub>OS</sub>	Change in Average TC with V <sub>OS</sub> Adjust	$R_S = 50\Omega$ , (Note 4)		0.5			0.5			0.5		μV/°C per mV
los	Input Offset Current	$T_j = 25$ °C, (Notes 3, 5) $T_j \le T_{HIGH}$		3	20 20		3	20 1		3	50 2	pA nA
I <sub>B</sub>	Input Bias Current	$T_j = 25$ °C, (Notes 3, 5) $T_j \le T_{HIGH}$		30	100 50		30	100 5		30	200 8	pA nA
R <sub>IN</sub>	Input Resistance	T <sub>j</sub> =25°C		10 <sup>12</sup>			10 <sup>12</sup>			10 <sup>12</sup>		Ω
A <sub>VOL</sub>	Large Signal Voltage Gain	$V_S = \pm 15V$ , $T_A = 25$ °C $V_O = \pm 10V$ , $R_L = 2k$ Over Temperature	50 25	200		50 25	200		25 15	200		V/mV V/mV
Vo	Output Voltage Swing	$V_S = \pm 15V, R_L = 10k$ $V_S = \pm 15V, R_L = 2k$	±12 ±10	± 13 ± 12		±12 ±10	± 13 ± 12		±12 ±10	±13 ±12		V
V <sub>CM</sub>	Input Common-Mode Voltage Range	V <sub>S</sub> = ±15V	±11	+15.1 -12		±11	±15.1 -12		+10	+15.1 -12		V V
CMRR	Common-Mode Rejection Ratio		85	100		85	100		80	100		dB
PSRR	Supply Voltage Rejection Ratio	(Note 6)	85	100		85	100		80	100		dB

#### **DC Electrical Characteristics** $T_A = T_j = 25^{\circ}C$ , $V_S = \pm 15V$

Parameter	LF155/ LF2 LF355/	:55,	LF	355		LF156A/156, LF256/356B		LF356A/356		LF157A/157 LF257/357B		LF357A/357	
	Тур	Max	Тур	Max	Тур	Max	Тур	Max	Тур	Max	Тур	Max	
Supply Current	2	4	2	4	5	7	5	10	5	7	5	10	mA

#### AC Electrical Characteristics $T_A = T_j = 25^{\circ}\text{C}, V_S = \pm 15\text{V}$

Symbol	Parameter	Conditions	LF155/255/ 355/355B	LF156/256, LF356B	LF156/256/ 356/356B	LF157/257, LF357B	LF157/257/ 357/357B	Units
			Тур	Min	Тур	Min	Тур	
SR	Slew Rate	LF155/6: A <sub>V</sub> =1, LF157: A <sub>V</sub> =5	5	7.5	12	30	50	V/μs V/μs
GBW	Gain Bandwidth Product		2.5		5		20	MHz
ts	Settling Time to 0.01%	(Note 7)	4		1.5		1.5	μs
e <sub>n</sub>	Equivalent Input Noise Voltage	R <sub>S</sub> =100Ω f=100 Hz f=1000 Hz	25 20		15 12		15 12	nV/√ <del>Hz</del> nV/√ <del>Hz</del>
i <sub>n</sub>	Equivalent Input Current Noise	f=100 Hz f=1000 Hz	0.01 0.01		0.01 0.01		0.01 0.01	pA/√Hz pA/√Hz
C <sub>IN</sub>	Input Capacitance		3		3		3	pF

#### **Notes for Electrical Characteristics**

Note 1: The maximum power dissipation for these devices must be derated at elevated temperatures and is dictated by  $T_{jMAX}$ ,  $\theta_{jA}$ , and the ambient temperature,  $T_A$ . The maximum available power dissipation at any temperature is  $P_d = (T_{jMAX} - T_A)/\theta_{jA}$  or the 25°C  $P_{dMAX}$ , whichever is less.

Note 2: Unless otherwise specified the absolute maximum negative input voltage is equal to the negative power supply voltage.

Note 3: Unless otherwise stated, these test conditions apply:

	LF155A/6A/7A LF155//6/7	LF255//6/7	LF355A/6A/7A	LF355B/6B/7B	LF355//6/7
Supply Voltage, V <sub>S</sub>	$\pm 15V \le V_S \le \pm 20V$	$\pm 15V \le V_S \le \pm 20V$	$\pm 15V \le V_S \le \pm 18V$	$\pm 15V \le V_S \pm 20V$	V <sub>S</sub> = ±15V
T <sub>A</sub>	$-55^{\circ}\text{C} \le \text{T}_{A} \le +125^{\circ}\text{C}$	$-25^{\circ}\text{C} \le \text{T}_{\text{A}} \le +85^{\circ}\text{C}$	$0^{\circ}C \le T_A \le +70^{\circ}C$	$0^{\circ}C \le T_{A} \le +70^{\circ}C$	$0^{\circ}C \le T_A \le +70^{\circ}C$
T <sub>HIGH</sub>	+125°C	+85°C	+70°C	+70°C	+70°C

and V<sub>OS</sub>, I<sub>B</sub> and I<sub>OS</sub> are measured at V<sub>CM</sub>=0.

Note 4: The Temperature Coefficient of the adjusted input offset voltage changes only a small amount (0.5µV/°C typically) for each mV of adjustment from its original unadjusted value. Common-mode rejection and open loop voltage gain are also unaffected by offset adjustment.

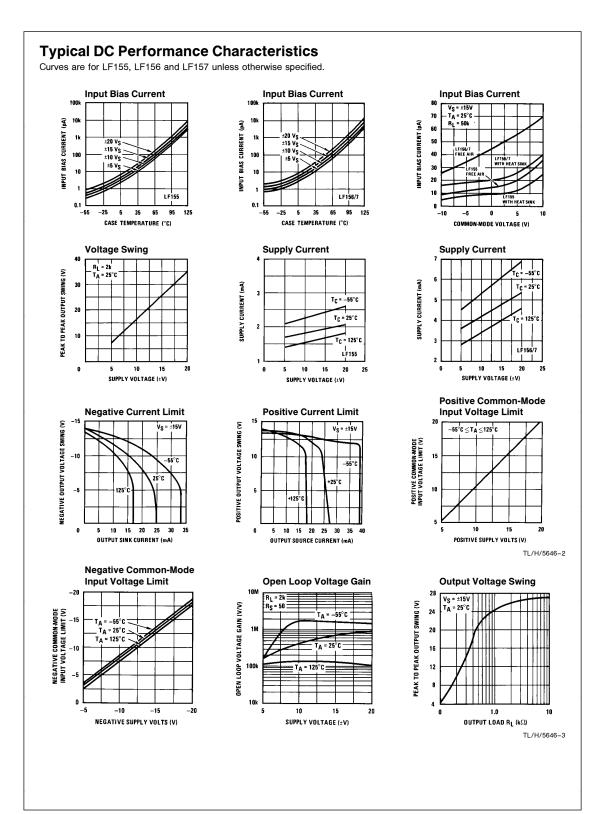
Note 5: The input bias currents are junction leakage currents which approximately double for every 10°C increase in the junction temperature,  $T_J$ . Due to limited production test time, the input bias currents measured are correlated to junction temperature. In normal operation the junction temperature rises above the ambient temperature as a result of internal power dissipation, Pd.  $T_j = T_A + \theta_{jA}$  Pd where  $\theta_{jA}$  is the thermal resistance from junction to ambient. Use of a heat sink is recommended if input bias current is to be kept to a minimum.

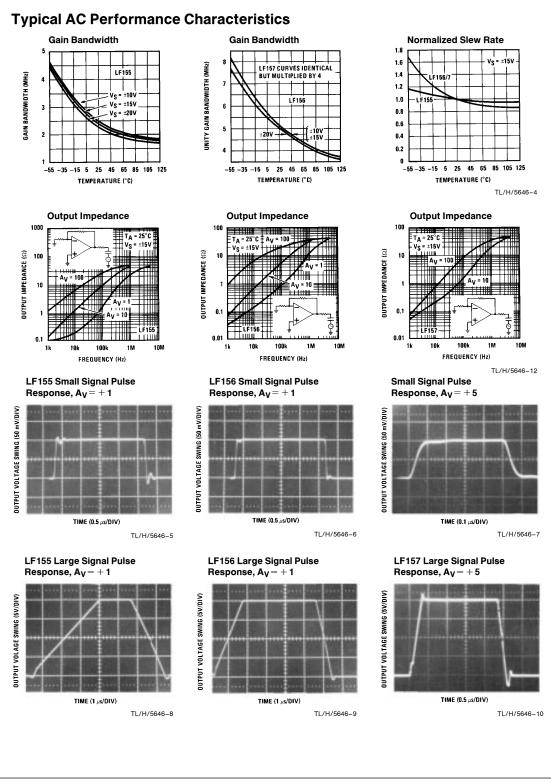
Note 6: Supply Voltage Rejection is measured for both supply magnitudes increasing or decreasing simultaneously, in accordance with common practice.

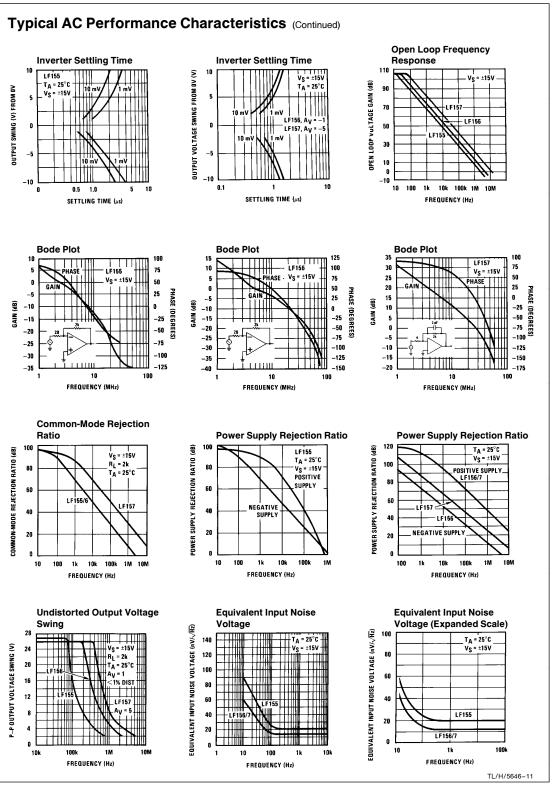
Note 7: Settling time is defined here, for a unity gain inverter connection using 2 k $\Omega$  resistors for the LF155/6. It is the time required for the error voltage (the voltage at the inverting input pin on the amplifier) to settle to within 0.01% of its final value from the time a 10V step input is applied to the inverter. For the LF157,  $A_V = -5$ , the feedback resistor from output to input is 2 k $\Omega$  and the output step is 10V (See Settling Time Test Circuit).

Note 8: Refer to RETS155AX for LF155A, RETS155X for LF155, RETS156AX for LF156A, RETS156X for LF156, RETS157A for LF157A and RETS157X for LF157 military specifications.

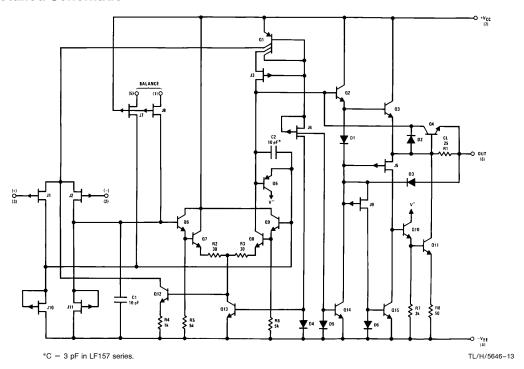
Note 9: Max. Power Dissipation is defined by the package characteristics. Operating the part near the Max. Power Dissipation may cause the part to operate outside guaranteed limits.





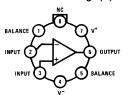


#### **Detailed Schematic**



#### **Connection Diagrams** (Top Views)

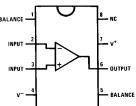
#### Metal Can Package (H)



TL/H/5646-14

Order Number LF156AH, LF155H, LF156H, LF255H, LF256H, LF257H, LF355AH, LF356AH, LF357AH, LF356BH, LF355H, LF356H, LF357H, LM155AH/883, LM155H/883, LM156AH/883, LM156H/883, LM157AH/883 or LM157H/883\* See NS Package Number H08C

#### Dual-In-Line Package (M and N)



TL/H/5646-29

Order Number LF355M, LF356M, LF357M, LF355BM, LF356BM, LF355BN, LF356BN, LF357BN, LF355N, LF356N or LF357N See NS Package Number M08A or N08E

\*Available per JM38510/11401 or JM38510/11402

#### **Application Hints**

The LF155/6/7 series are op amps with JFET input devices. These JFETs have large reverse breakdown voltages from gate to source and drain eliminating the need for clamps across the inputs. Therefore large differential input voltages can easily be accomodated without a large increase in input current. The maximum differential input voltage is independent of the supply voltages. However, neither of the input voltages should be allowed to exceed the negative supply as this will cause large currents to flow which can result in a destroyed unit.

Exceeding the negative common-mode limit on either input will force the output to a high state, potentially causing a reversal of phase to the output. Exceeding the negative common-mode limit on both inputs will force the amplifier output to a high state. In neither case does a latch occur since raising the input back within the common-mode range again puts the input stage and thus the amplifier in a normal operating mode.

Exceeding the positive common-mode limit on a single input will not change the phase of the output however, if both inputs exceed the limit, the output of the amplifier will be forced to a high state.

These amplifiers will operate with the common-mode input voltage equal to the positive supply. In fact, the common-mode voltage can exceed the positive supply by approximately 100 mV independent of supply voltage and over the full operating temperature range. The positive supply can therefore be used as a reference on an input as, for example, in a supply current monitor and/or limiter.

Precautions should be taken to ensure that the power supply for the integrated circuit never becomes reversed in polarity or that the unit is not inadvertently installed backwards in a socket as an unlimited current surge through the resulting forward diode within the IC could cause fusing of the internal conductors and result in a destroyed unit.

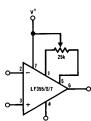
All of the bias currents in these amplifiers are set by FET current sources. The drain currents for the amplifiers are therefore essentially independent of supply voltage.

As with most amplifiers, care should be taken with lead dress, component placement and supply decoupling in order to ensure stability. For example, resistors from the output to an input should be placed with the body close to the input to minimize "pickup" and maximize the frequency of the feedback pole by minimizing the capacitance from the input to ground.

A feedback pole is created when the feedback around any amplifier is resistive. The parallel resistance and capacitance from the input of the device (usually the inverting input) to ac ground set the frequency of the pole. In many instances the frequency of this pole is much greater than the expected 3 dB frequency of the closed loop gain and consequently there is negligible effect on stability margin. However, if the feedback pole is less than approximately six times the expected 3 dB frequency a lead capacitor should be placed from the output to the input of the op amp. The value of the added capacitor should be such that the RC time constant of this capacitor and the resistance it parallels is greater than or equal to the original feedback pole time constant.

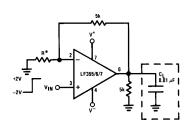
#### **Typical Circuit Connections**

#### V<sub>OS</sub> Adjustment



- V<sub>OS</sub> is adjusted with a 25k potentiometer
- The potentiometer wiper is connected to V<sup>+</sup>
- For potentiometers with temperature coefficient of 100 ppm/°C or less the additional drift with adjust is ≈ 0.5 μV/°C/mV of adjustment
- • Typical overall drift: 5  $\mu$ V/°C  $\pm$  (0.5  $\mu$ V/°C/mV of adj.)

#### **Driving Capacitive Loads**



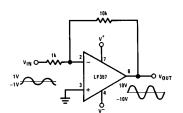
\*LF155/6 R=5k LF157 R=1.25k

Due to a unique output stage design, these amplifiers have the ability to drive large capacitive loads and still maintain stability.  $C_{L(MAX)} \simeq 0.01$ 

Overshoot ≤ 20%

Settling time (t<sub>s</sub>)  $\approx$  5  $\mu$ s

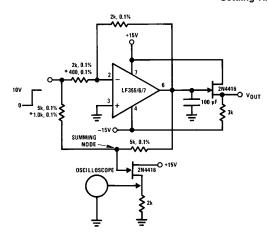
#### LF157. A Large Power BW Amplifier



TL/H/5646-15 For distortion  $\leq$  1% and a 20 Vp-p V\_{OUT} swing, power bandwidth is: 500 kHz.

# **Typical Applications**

#### **Settling Time Test Circuit**

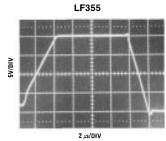


- Settling time is tested with the LF155/6 connected as unity gain inverter and LF157 connected for
- $A_V = -5$ FET used to isolate the probe capacitance
- Output = 10V step
- $\bullet \quad A_V = \, -5 \text{ for LF157}$

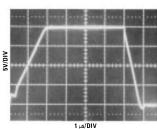
TL/H/5646-16

#### Large Signal inverter Output, $V_{\mbox{OUT}}$ (from Settling Time Circuit)

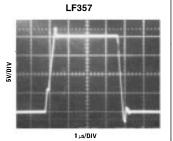
LF356







TL/H/5646-18



TL/H/5646-19

#### Low Drift Adjustable Voltage Reference

- 2N4118

  P1
  250k

  V<sup>+</sup> = 15V

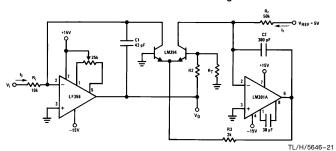
  V<sub>0UT</sub> = 10V

  R1
  180k

  R2
  300k

  R3
  180k
- Δ V<sub>OUT</sub>/ΔT = ±0.002%/°C
- All resistors and potentiometers should be wire-wound
- P1: drift adjust
- P2: V<sub>OUT</sub> adjust
- Use LF155 for
- Low I<sub>B</sub>
- Low drift
- Low supply current

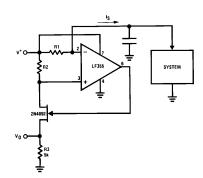
#### Fast Logarithmic Converter



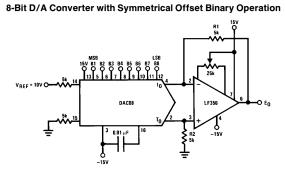
- • Dynamic range: 100  $\mu A \leq I_i \leq$  1 mA (5 decades),  $\left| V_O \right| = 1 V / decade$
- Transient response: 3  $\mu s$  for  $\Delta I_i = 1$  decade
- C1, C2, R2, R3: added dynamic compensation
- V<sub>OS</sub> adjust the LF156 to minimize quiescent error
- R<sub>T</sub>: Tel Labs type Q81 + 0.3%/°C

$$|V_{OUT}| = \left[1 + \frac{R2}{R_T}\right] \frac{kT}{q} ln \ V_i \left[\frac{R_f}{V_{REF \, Ri}}\right] = log \ V_i \frac{1}{R_i l_T} R2 = 15.7 k, R_T = 1 k, 0.3 \%/^{\circ} C \ (for temperature compensation)$$

#### **Precision Current Monitor**



- V<sub>O</sub>=5 R1/R2 (V/mA of I<sub>S</sub>)
- R1, R2, R3: 0.1% resistors
- Use LF155 for
  - Common-mode range to supply range
  - Low I<sub>B</sub>
  - Low V<sub>OS</sub>
  - Low Supply Current

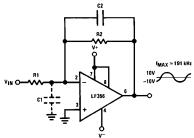


TL/H/5646-31

- $\bullet~$  R1, R2 should be matched within  $\pm\,0.05\,\%$
- Full-scale response time: 3μs

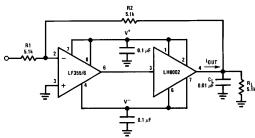
Eo	В1	B2	Вз	В4	В5	В6	В7	В8	Comments
+9.920	1	1	1	1	1	1	1	1	Positive Full-Scale
+0.040	1	0	0	0	0	0	0	0	(+) Zero-Scale
-0.040	0	1	1	1	1	1	1	1	(-) Zero-Scale
-9.920	0	0	0	0	0	0	0	0	Negative Full-Scale

#### Wide BW Low Noise, Low Drift Amplifier



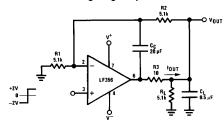
- ullet Power BW:  $f_{MAX} = \frac{S_f}{2\pi V_P} \cong$  191 kHz
- Parasitic input capacitance C1 ≈ (3 pF for LF155, LF156 and LF157 plus any additional layout capacitance) interacts with feedback elements and creates undesirable high frequency pole. To compensate add C2 such that: R2 C2 ≈ R1 C1.

#### Boosting the LF156 with a Current Amplifier



- I<sub>OUT(MAX)</sub>  $\cong$  150 mA (will drive R<sub>L</sub>  $\geq$  100 $\Omega$ )
- $\frac{\Delta V_{OUT}}{\Delta T} = \frac{0.15}{10^{-2}} V/\mu s$  (with C<sub>L</sub> shown)
- No additional phase shift added by the current amplifier

#### **Isolating Large Capacitive Loads**



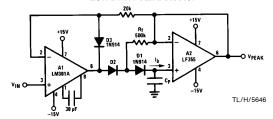
Overshoot 6%

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- t<sub>s</sub> 10 μs
- $\bullet$  When driving large  $C_L,$  the  $V_{OUT}$  slew rate determined by  $C_L$  and  $I_{OUT(MAX)}\!\!:$

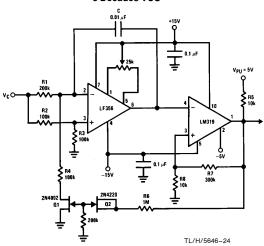
$$\frac{\Delta V_{OUT}}{\Delta T} = \frac{I_{OUT}}{C_L} \simeq \frac{0.02}{0.5} \, \text{V/} \mu \text{s} = 0.04 \, \text{V/} \mu \text{s} \, \text{(with $C_L$ shown)}$$

#### **Low Drift Peak Detector**



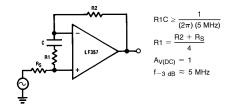
- • By adding D1 and R $_{\rm f}$ , V $_{\rm D1}$ =0 during hold mode. Leakage of D2 provided by feedback path through R $_{\rm f}$ .
- Leakage of circuit is essentially I<sub>b</sub> (LF155, LF156) plus capacitor leakage of Cp.
- $\bullet$  Diode D3 clamps  $V_{OUT}$  (A1) to  $V_{IN} V_{D3}$  to improve speed and to limit reverse bias of D2.
- Maximum input frequency should be  $<<1/_2\pi R_f C_{D2}$  where  $C_{D2}$  is the shunt capacitance of D2.

#### 3 Decades VCO

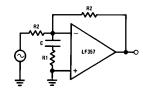


- $f = \frac{V_{C} \left(R8 + R7\right)}{\left(8 \ V_{PU} \ R8 \ R1\right) \ C}, \\ 0 \! \leq \! V_{C} \! \leq \! 30V, \ 10 \ Hz \! \leq \! f \! \leq \! 10 \ kHz$
- R1, R4 matched. Linearity 0.1% over 2 decades.

#### Non-Inverting Unity Gain Operation for LF157



#### **Inverting Unity Gain for LF157**



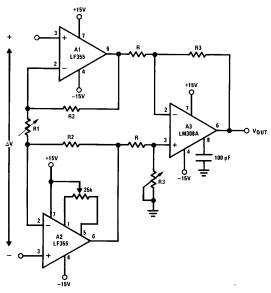
$$R1C \ge \frac{1}{(2\pi) (5 \text{ MHz})}$$

$$R1 = \frac{R2}{4}$$

$$A_{V(DC)} = -1$$

 $f_{-3 \text{ dB}} \approx 5 \text{ MHz}$  TL/H/5646-25

#### High Impedance, Low Drift Instrumentation Amplifier



 $\bullet \quad V_{OUT} = \frac{R3}{R} \left[ \frac{2R2}{R1} + 1 \right] \Delta V, V^- \, + \, 2V \leq V_{IN} \, common\text{-mode} \leq V^+$ 

- System V<sub>OS</sub> adjusted via A2 V<sub>OS</sub> adjust
- Trim R3 to boost up CMRR to 120 dB. Instrumentation amplifier resistor array recommended for best accuracy and lowest drift

# 

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- Both amplifiers (A1, A2) have feedback loops individually closed with stable responses (overshoot negligible)
- Acquisition time T<sub>A</sub>, estimated by:

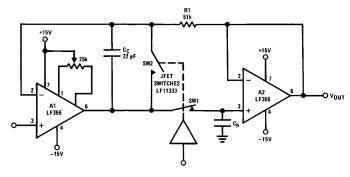
Acquisition time 
$$I_A$$
, estimated by:  
 $T_A \simeq \left[\frac{2R_{ON}, V_{IN}, C_h}{S_r}\right]^{\frac{1}{2}}$  provided that:

$$V_{IN} < 2\pi S_r \, R_{ON} \, C_h \text{ and } T_A > \frac{V_{IN} \, C_h}{I_{OUT(MAX)}}, R_{ON} \, \text{is of SW1}$$

If inequality not satisfied: 
$$T_A \simeq \frac{V_{IN} C_h}{20 \text{ mA}}$$

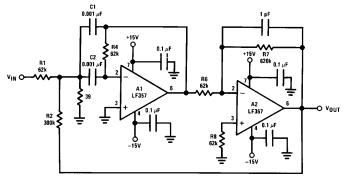
- $\bullet$  LF156 develops full  $S_r$  output capability for  $V_{IN}\!\ge\!1V$
- Addition of SW2 improves accuracy by putting the voltage drop across SW1 inside the feedback loop
- Overall accuracy of system determined by the accuracy of both amplifiers, A1 and A2

#### **High Accuracy Sample and Hold**



- By closing the loop through A2, the V<sub>OUT</sub> accuracy will be determined uniquely by A1.
   No V<sub>OS</sub> adjust required for A2.
- T<sub>A</sub> can be estimated by same considerations as previously but, because of the added propagation delay in the feedback loop (A2) the overshoot is not negligible.
- Overall system slower than fast sample and hold
- $\bullet$  R1, C<sub>C</sub>: additional compensation
- Use LF156 for
- Fast settling time
- Low V<sub>OS</sub>

#### High Q Band Pass Filter



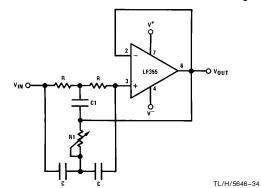
- By adding positive feedback (R2) Q increases to 40
- f<sub>BP</sub>=100 kHz

$$\frac{V_{OUT}}{V_{IN}} = 10\sqrt{\overline{Q}}$$

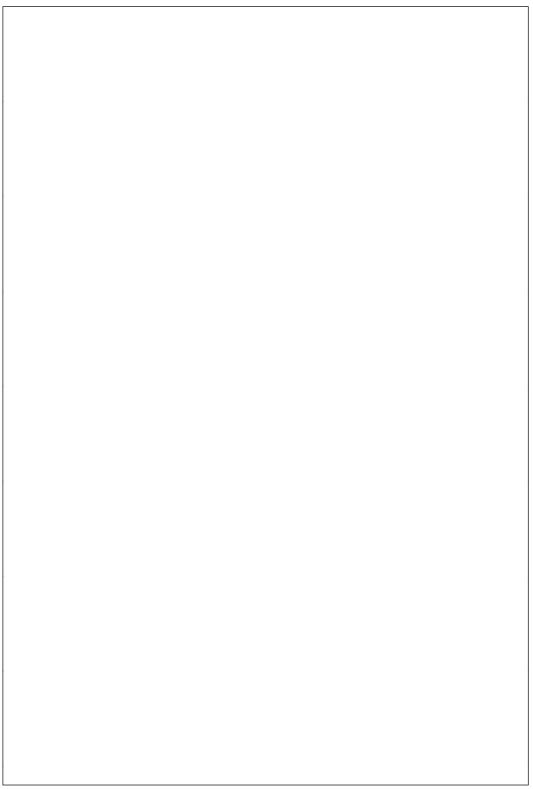
- Clean layout recommended
- Response to a 1 Vp-p tone burst: 300  $\mu$ s

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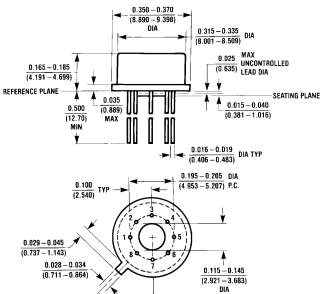
#### High Q Notch Filter



- $2R1 = R = 10 M\Omega$ 2C = C1 = 300 pF
- Capacitors should be matched to obtain high Q
- $\bullet$  f<sub>NOTCH</sub> = 120 Hz, notch = -55 dB, Q > 100
- Use LF155 for
- Low I<sub>B</sub>
- Low supply current

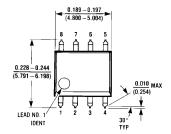




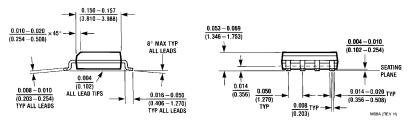


Metal Can Package (H) Order Number LF156AH, LF155H, LF156H, LF255H, LF256H, LF257H, LF355AH, LF356AH, LF357AH, LF356BH, LF355H, LF356H or LF357H NS Package Number H08C

45° EQUALLY SPACED

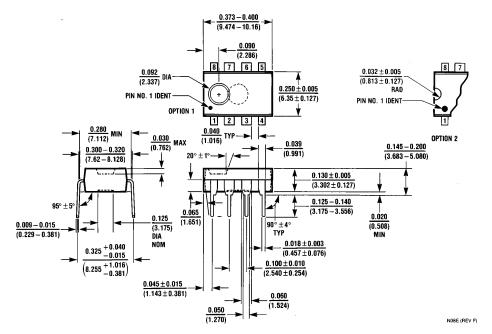


HOSC (REV E)



Small Outline Package (M) Order Number LF355M, LF356M, LF357M, LF355BM or LF356BM NS Package Number M08A

#### Physical Dimensions inches (millimeters) (Continued)



Molded Dual-In-Line Package (N) Order Number LF355N, LF356N, LF357N, LF355BN, LF356BN, LF357BN NS Package Number N08E

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